Response to Missing Parts

PTO/SB/21 (05-03) Approved for use through 04/30/2003. OMB 0651-0031 U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number Application Number 09/955,810 TRANSMITTAL Filing Date September 19, 2001 **FORM** First Named Inventor Yoshiyuki Tanaka, et al. Art Unit 2825 (to be used for all correspondence after initial filing) **Examiner Name** Lee Calvin Attorney Docket Number 075834.00111 Total Number of Pages in This Submission **ENCLOSURES** (Check all that apply) After Allowance communication Fee Transmittal Form Drawing(s) to Group Appeal Communication to Board Licensing-related Papers Fee Attached of Appeals and Interferences Appeal Communication to Group (Appeal Notice, Brief, Reply Brief) Amendment/Reply Petition to Convert to a Proprietary Information Provisional Application After Final Power of Attorney, Revocation Status Letter Change of Correspondence Address Affidavits/declaration(s) Other Enclosure(s) (please Terminal Disclaimer Extension of Time Request Identify below): Post Card Request for Refund **Express Abandonment Request** CD, Number of CD(s) Information Disclosure Statement Remarks Certified Copy of Priority Document(s) The Commissioner is hereby authorized technarge any fees due or to credit any overpayment to Deposit Account Response to Missing Parts/ Incomplete Application No. 50-1794.

under 37 CFR 1.52 or 1.53 SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT Firm Robert J. Depke, Holland & Knight LLC 131 South Dearborn Street, 30th Floor, Chicago, IL 60603 Individual name Signature Date

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THE UNITED STATES PATENT AND TRADEMARK OFFICE

Yoshiyuki Tanaka et al.

Atty. Docket No.

075834.00111

Serial No.:

Applicants:

09/ 955,810

Group Art Unit:

2825

Filed:

September 19, 2001

Examiner:

Lee Calvin

Invention:

"PRODUCTION METHOD OF SEMICONDUCTOR DEVICE"

Assistant Commissioner of Patents

SIR:

AMENDMENT B

ant Commissioner of Patents
Alexandria, VA 22313-1450

In response to the Office Action dated May 21, 2003, please amend the application as follows:

IN THE CLAIMS:

(Previously Amended) A method for producing a semiconductor device including formation of an interlayer insulating film having a fluorine-doped silicon oxide layer above a substrate, the method comprising the steps of:

forming said fluorine-doped silicon oxide layer in a process chamber; and

forming a silicon oxide layer on said fluorine-doped silicon oxide layer in a same process chamber subsequent to formation of said fluorine-doped silicon oxide layer, said silicon oxide layer being formed at a temperature at least 10% higher than a film forming temperature of said fluorine-doped silicon oxide layer; thereby

forming said interlayer insulating film comprising said fluorine-doped silicon oxide layer and said silicon oxide layer formed thereon.

2. (Original) The method for producing a semiconductor device according to claim 1, wherein

a film forming temperature of said silicon oxide layer is equal or less than 450 °C.